

## Silicon NPN Power Transistors

2SC2611

## DESCRIPTION

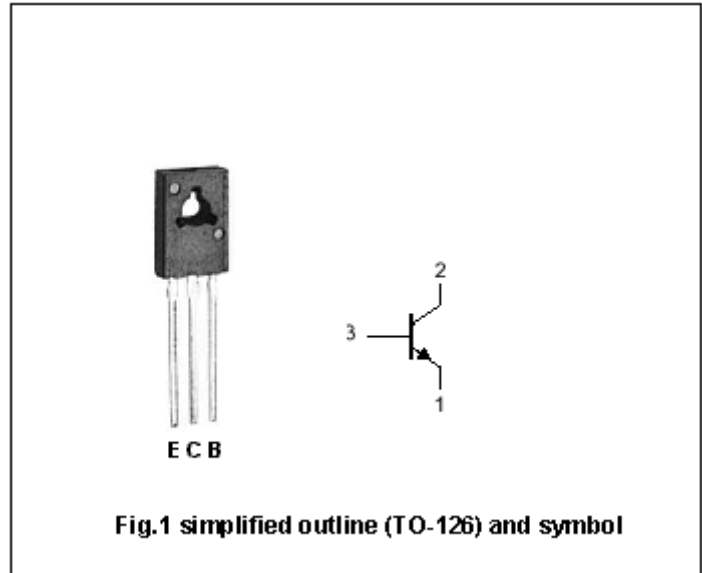
- With TO-126 package
- High breakdown voltage

## APPLICATIONS

- For high voltage amplifier TV video output applications

## PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

ABSOLUTE MAXIMUM RATINGS( $T_c=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	300	V
$V_{CEO}$	Collector-emitter voltage	Open base	300	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		0.1	A
$P_C$	Collector power dissipation	$T_a=25^\circ\text{C}$	1.25	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =1mA; R <sub>BE</sub> =∞	300			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =10 μ A; I <sub>E</sub> =0	300			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10 μ A; I <sub>C</sub> =0	5			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =20mA; I <sub>B</sub> =2mA			1.5	V
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =250V; R <sub>BE</sub> =∞			1.0	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =20mA ; V <sub>CE</sub> =20V	30		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =20mA ; V <sub>CE</sub> =20V	50	80		MHz
C <sub>OB</sub>	Collector output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =20V; f=1MHz			4.0	pF

PACKAGE OUTLINE

